



JCT616FH 16A SCR

Rev.A.1.1

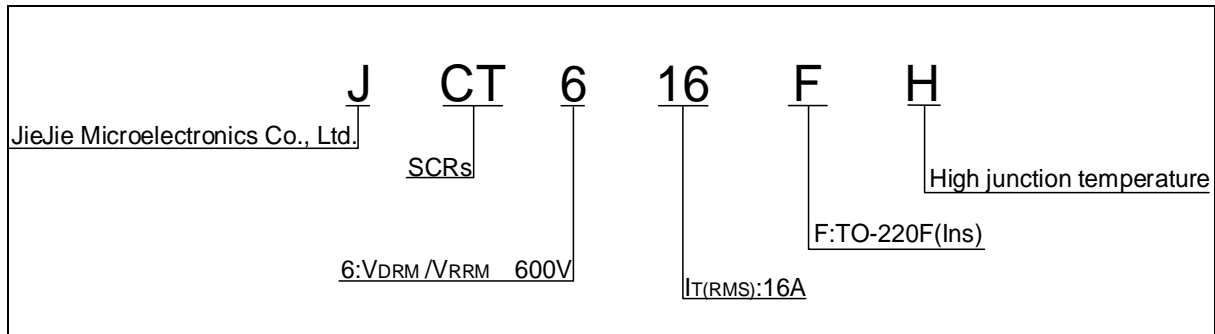
DESCRIPTION:

With high ability to withstand



Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ORDERING INFORMATION



MARKING

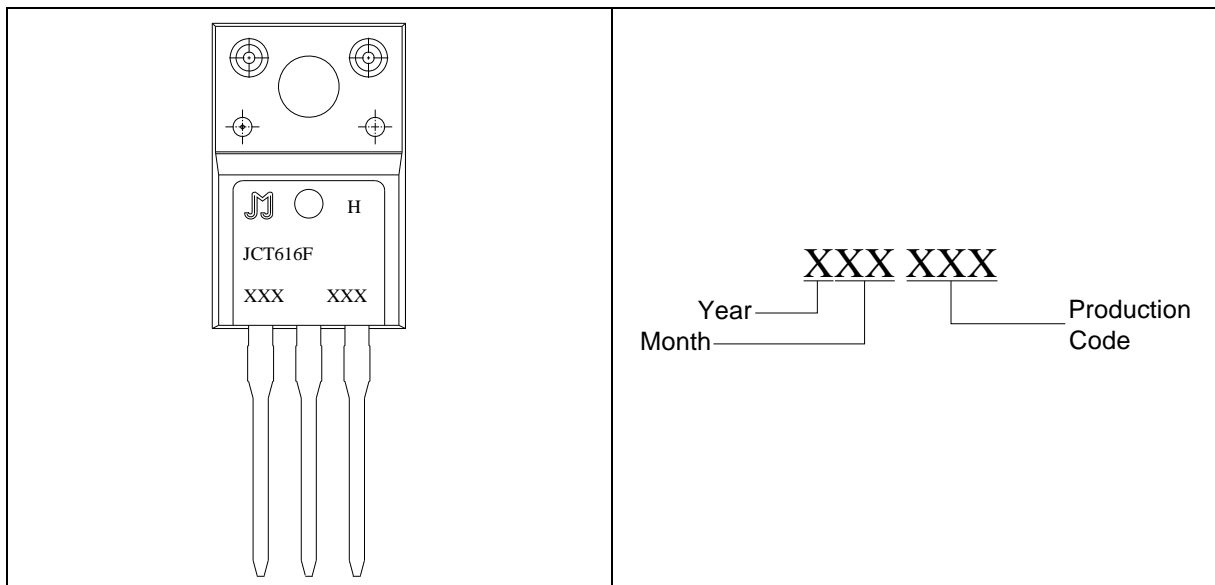


FIG.1: Maximum power dissipation versus RMS on-state current

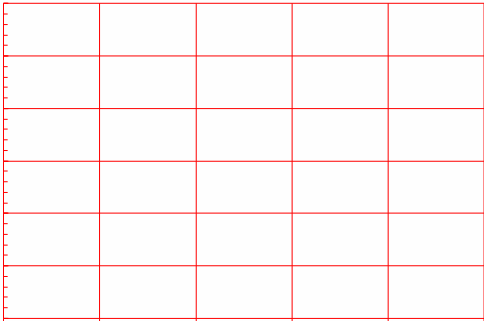


FIG.2: RMS on-state current versus case temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT616FH	600	15	TO-220F(Ins)	50	Tube


Document Revision History

Date	Revision	Changes
Jun.15, 2023	A.1.0	Last update
Oct.17, 2022	0`	

PACKAGE MECHANICAL DATA



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